

# **NX7002BKSX Datasheet**

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DiGi Electronics Part Number NX7002BKSX-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number NX7002BKSX

Description MOSFET N-CH 60V 270MA 6TSSOP

Detailed Description N-Channel 60 V 270mA (Ta) 310mW (Ta), 1.67W (Tc

) Surface Mount 6-TSSOP



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# **Purchase and inquiry**

| Manufacturer Product Number:            | Manufacturer:                           |
|---|---|
| NX7002BKSX                              | Nexperia USA Inc.                       |
| Series:                                 | Product Status:                         |
|   | Active                                  |
| FET Type:                               | Technology:                             |
| N-Channel                               | MOSFET (Metal Oxide)                    |
| Drain to Source Voltage (Vdss):         | Current - Continuous Drain (Id) @ 25°C: |
| 60 V                                    | 270mA (Ta)                              |
| Drive Voltage (Max Rds On, Min Rds On): | Rds On (Max) @ ld, Vgs:                 |
| 5V, 10V                                 | 2.80hm @ 200mA, 10V                     |
| Vgs(th) (Max) @ Id:                     | Gate Charge (Qg) (Max) @ Vgs:           |
| 2.1V @ 250µA                            | 1 nC @ 10 V                             |
| Vgs (Max):                              | Input Capacitance (Ciss) (Max) @ Vds:   |
| ±20V                                    | 23.6 pF @ 10 V                          |
| FET Feature:                            | Power Dissipation (Max):                |
|   | 310mW (Ta), 1.67W (Tc)                  |
| Operating Temperature:                  | Mounting Type:                          |
| -55°C ~ 150°C (TJ)                      | Surface Mount                           |
| Supplier Device Package:                | Package / Case:                         |
| 6-TSSOP                                 | 6-TSSOP, SC-88, SOT-363                 |
| Base Product Number:                    |   |
| NX7002                                  |   |

# **Environmental & Export classification**

8541.29.0095

| RoHS Status:     | Moisture Sensitivity Level (MSL): |
|------------------|-----------------------------------|
| ROHS3 Compliant  | 1 (Unlimited)                     |
| REACH Status:    | ECCN:                             |
| REACH Unaffected | EAR99                             |
| HTSUS:           |                                   |



# **NX7002BKS**

# 60 V, dual N-channel Trench MOSFET 12 May 2015

**Product data sheet** 

## 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

## 3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions                                       |     | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| Per transistor    |                                  |  |     |     |     |     |      |
| V <sub>DS</sub>   | drain-source voltage             | T <sub>j</sub> = 25 °C                           |     | -   | -   | 60  | V    |
| $V_{GS}$          | gate-source voltage              |  |     | -20 | -   | 20  | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C  |     | -   | -   | 330 | mA   |
|                   |                                  | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C | [1] | -   | -   | 240 | mA   |
| Static charact    | eristics (per transistor)        |  |     |     |     | '   | ,    |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS}$ = 10 V; $I_D$ = 200 mA; $T_j$ = 25 °C   |     | -   | 2.2 | 2.8 | Ω    |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



60 V, dual N-channel Trench MOSFET

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline               | Graphic symbol     |
|-----|--------|-------------|----------------------------------|--------------------|
| 1   | S1     | source TR1  | 654                              | D1 D2              |
| 2   | G1     | gate TR1    |                                  |                    |
| 3   | D2     | drain TR2   | 0                                | G1 $G2$ $G2$       |
| 4   | S2     | source TR2  | ☐1 ☐2 ☐3<br><b>————</b> (2.2—22) |                    |
| 5   | G2     | gate TR2    | TSSOP6 (SOT363)                  |                    |
| 6   | D1     | drain TR1   |                                  | S1 S2<br>017aaa256 |

# 6. Ordering information

Table 3. Ordering information

| Type number |           | Package | e  |         |  |  |
|-------------|-----------|---------|--|---------|--|--|
|             |           | Name    | Description                              | Version |  |  |
|             | NX7002BKS | TSSOP6  | plastic surface-mounted package; 6 leads | SOT363  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code [1] |
|-------------|------------------|
| NX7002BKS   | LT%              |

[1] % = placeholder for manufacturing site code

60 V, dual N-channel Trench MOSFET

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |     | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|-----|------|
| Per transis      | tor                     |   |     |     |     |      |
| $V_{DS}$         | drain-source voltage    | T <sub>j</sub> = 25 °C                              |     | -   | 60  | V    |
| $V_{GS}$         | gate-source voltage     |   |     | -20 | 20  | V    |
| I <sub>D</sub>   | drain current           | $V_{GS}$ = 10 V; $T_{sp}$ = 25 °C                   |     | -   | 330 | mA   |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C    | [1] | -   | 240 | mA   |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C   | [1] | -   | 150 | mA   |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$ |     | -   | 0.8 | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                            | [2] | -   | 285 | mW   |
|                  |                         |   | [1] | -   | 320 | mW   |
|                  |                         | T <sub>sp</sub> = 25 °C                             |     | -   | 870 | mW   |
| Source-dra       | in diode                |   |     |     |     |      |
| Is               | source current          | T <sub>amb</sub> = 25 °C                            | [1] | -   | 200 | mA   |
| Per device       |                         | ,   | '   |     |     | '    |
| Tj               | junction temperature    |   |     | -55 | 150 | °C   |
| T <sub>amb</sub> | ambient temperature     |   |     | -55 | 150 | °C   |
| T <sub>stg</sub> | storage temperature     |   |     | -65 | 150 | °C   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

#### 60 V, dual N-channel Trench MOSFET

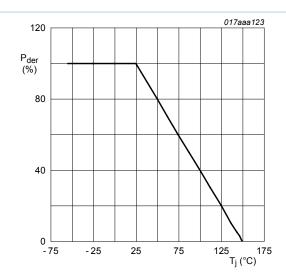


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times \textbf{100 \%}$$

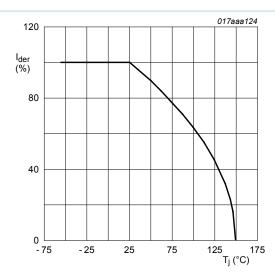


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

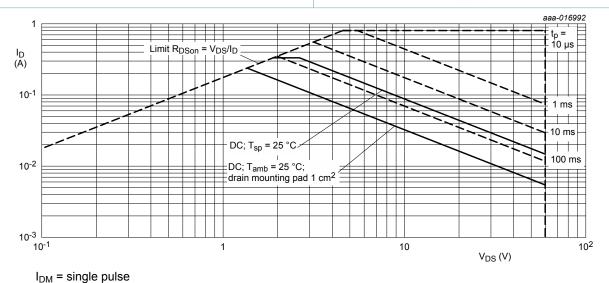


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

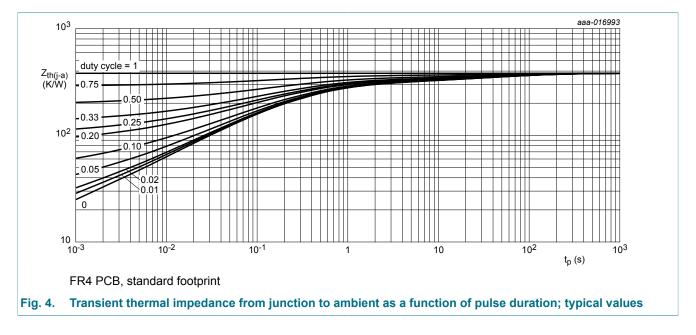
60 V, dual N-channel Trench MOSFET

## 9. Thermal characteristics

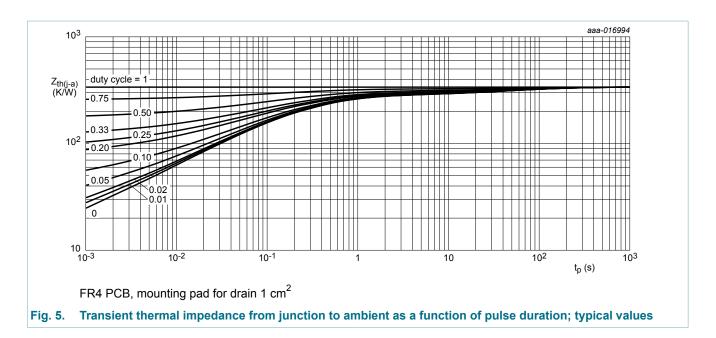
Table 6. Thermal characteristics

| Symbol                   | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|--------------------------|--|-------------|-----|-----|-----|-----|------|
| Per transistor           |  |             |     |     |     |     |      |
| R <sub>th(j-a)</sub>     | thermal resistance                               | in free air | [1] | -   | 380 | 440 | K/W  |
| from junction to ambient |  | [2]         | -   | 340 | 390 | K/W |      |
| R <sub>th(j-sp)</sub>    | thermal resistance from junction to solder point |             |     | -   | 125 | 145 | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



#### 60 V, dual N-channel Trench MOSFET



6/16

**60 V, dual N-channel Trench MOSFET** 

## 10. Characteristics

Table 7 Characteristics

| Symbol   | Parameter  | Conditions   | Min                                   | Тур  | Max  | Unit |
|--|--|--|---------------------------------------|------|------|------|
| Static cha   | racteristics (per transistor)  |  | , , , , , , , , , , , , , , , , , , , |      |      |      |
| $V_{(BR)DSS}$                                      | drain-source<br>breakdown voltage                                      | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C   | 60                                    | -    | -    | V    |
| $V_{GSth}$   | gate-source threshold voltage  | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                  | 1.1                                   | 1.6  | 2.1  | V    |
| I <sub>DSS</sub>                                   | drain leakage current  | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -                                     | -    | 1    | μΑ   |
| I <sub>GSS</sub>                                   | gate leakage current   | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -                                     | -    | 10   | μA   |
|  |  | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -                                     | -    | -10  | μΑ   |
|  |  | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -                                     | -    | 1    | μA   |
|  |  | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -                                     | -    | -1   | μA   |
|  |  | $V_{GS} = 5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$  | -                                     | -    | 0.3  | μA   |
|  |  | $V_{GS}$ = -5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                           | -                                     | -    | -0.3 | μA   |
| R <sub>DSon</sub> drain-source on-state resistance |  | $V_{GS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C                       | -                                     | 2.2  | 2.8  | Ω    |
|  |  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C | -                                     | 4.5  | 5.7  | Ω    |
|  | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C | -  | 2.5                                   | 3.2  | Ω    |      |
| 9 <sub>fs</sub>                                    | forward transconductance   | $V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C                       | -                                     | 600  | -    | mS   |
| $R_G$  | gate resistance  | f = 1 MHz  | -                                     | 2.5  | -    | Ω    |
| Dynamic c  | characteristics (per transist  | or)  | ,                                     |      |      |      |
| Q <sub>G(tot)</sub>                                | total gate charge  | V <sub>DS</sub> = 30 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V; | -                                     | 1    | -    | nC   |
| $Q_{GS}$   | gate-source charge   | T <sub>j</sub> = 25 °C   | -                                     | 0.12 | -    | nC   |
| $Q_{GD}$   | gate-drain charge  |  | -                                     | 0.18 | -    | nC   |
| C <sub>iss</sub>                                   | input capacitance  | V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                | -                                     | 23.6 | -    | pF   |
| C <sub>oss</sub>                                   | output capacitance   | T <sub>j</sub> = 25 °C   | -                                     | 4.6  | -    | pF   |
| C <sub>rss</sub>                                   | reverse transfer capacitance   |  | -                                     | 3    | -    | pF   |
| t <sub>d(on)</sub>                                 | turn-on delay time   | V <sub>DS</sub> = 50 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V; | -                                     | 4.7  | -    | ns   |
| t <sub>r</sub>                                     | rise time  | $R_{G(ext)} = 6 \Omega$ ; $T_j = 25 ^{\circ}C$                           | -                                     | 4.3  | -    | ns   |
| t <sub>d(off)</sub>                                | turn-off delay time  |  | -                                     | 6.9  | -    | ns   |
| t <sub>f</sub>                                     | fall time  |  | -                                     | 2.9  | -    | ns   |
| Source-dra   | ain diode (per transistor)   |  | I                                     | 1    | 1    |      |
| V <sub>SD</sub>                                    | source-drain voltage   | $I_S = 50 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$   | -                                     | 0.87 | 1.2  | V    |

#### 60 V, dual N-channel Trench MOSFET

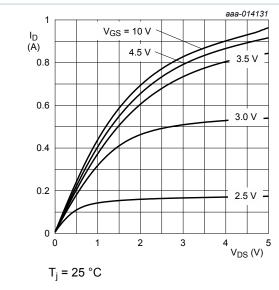
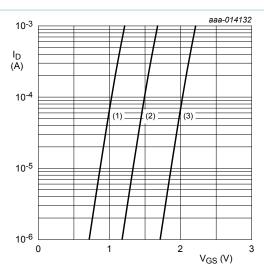


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i$  = 25 °C;  $V_{DS}$  = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

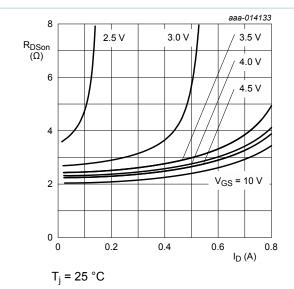
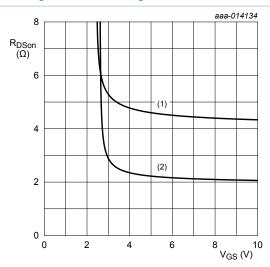


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



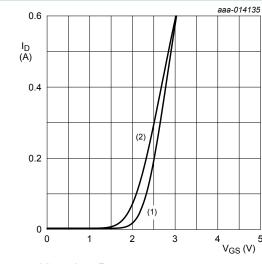
 $I_D = 0.2 A$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 60 V, dual N-channel Trench MOSFET



 $V_{DS} > I_D \times R_{DSon}$ (1)  $T_i = 25 \, ^{\circ}C$ 

(2)  $T_i = 150 \,^{\circ}\text{C}$ 

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

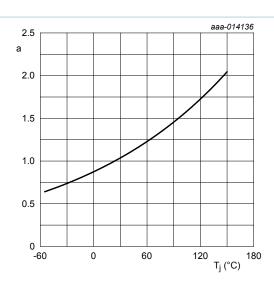
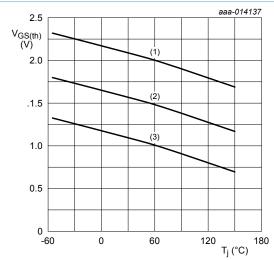


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

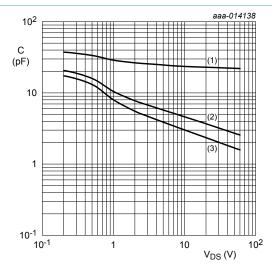
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 60 V, dual N-channel Trench MOSFET

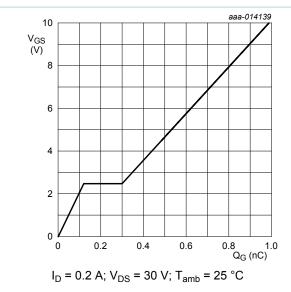


Fig. 14. Gate-source voltage as a function of gate charge; typical values

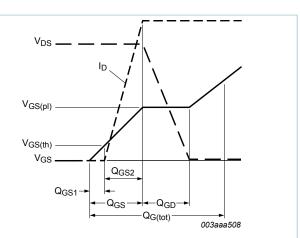
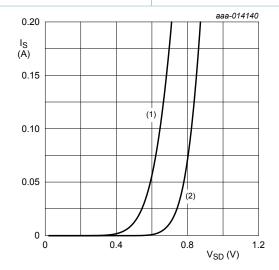


Fig. 15. MOSFET transistor: Gate charge waveform definitions



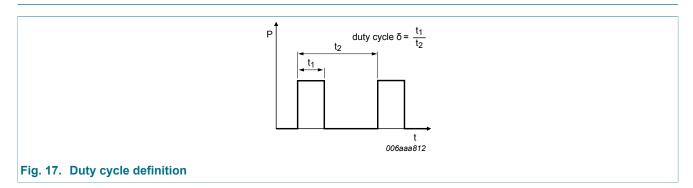
 $V_{GS} = 0 V$ (1)  $T_i = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \,^{\circ}\text{C}$ 

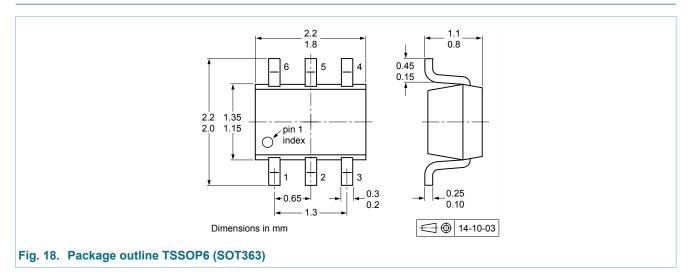
Fig. 16. Source current as a function of source-drain voltage; typical values

60 V, dual N-channel Trench MOSFET

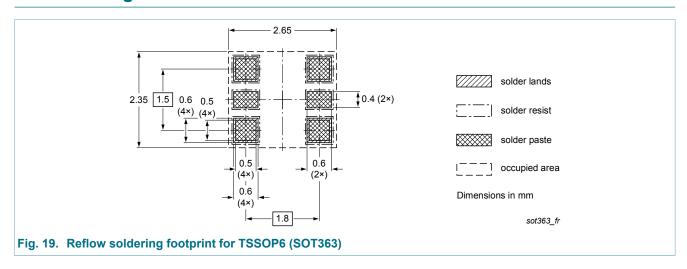
## 11. Test information



# 12. Package outline



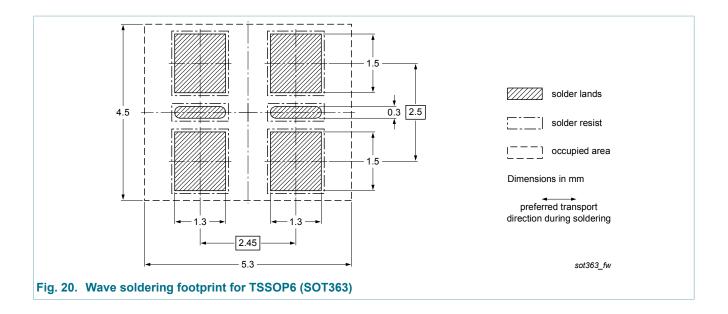
## 13. Soldering



NX7002BKS

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## **60 V, dual N-channel Trench MOSFET**



**60 V, dual N-channel Trench MOSFET** 

# 14. Revision history

#### Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| NX7002BKS v.1 | 20150512     | Product data sheet | -             | -          |

#### 60 V, dual N-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## 16. Contents

| 1    | General description     | 1  |
|------|-------------------------|----|
| 2    | Features and benefits   | 1  |
| 3    | Applications            | 1  |
| 4    | Quick reference data    | 1  |
| 5    | Pinning information     | 2  |
| 6    | Ordering information    | 2  |
| 7    | Marking                 | 2  |
| 8    | Limiting values         | 3  |
| 9    | Thermal characteristics | 5  |
| 10   | Characteristics         | 7  |
| 11   | Test information        | 11 |
| 12   | Package outline         | 11 |
| 13   | Soldering               | 11 |
| 14   | Revision history        | 13 |
| 15   | Legal information       | 14 |
| 15.1 | Data sheet status       | 14 |
| 15.2 | Definitions             | 14 |
| 15.3 | Disclaimers             | 14 |
| 15.4 | Trademarks              | 15 |

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